



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

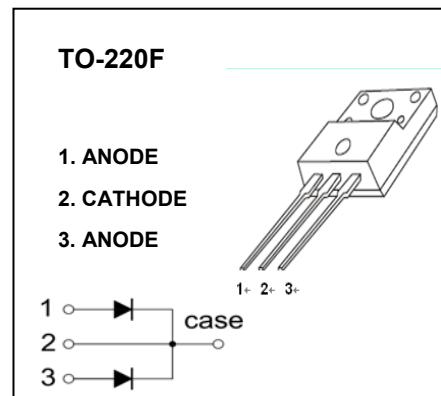
TO-220F Plastic-Encapsulate Diodes

MBR3030, 35, 40, 45, 50FCT

SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value					Unit
		MBR30 30FCT	MBR30 35FCT	MBR30 40FCT	MBR30 45FCT	MBR30 50FCT	
V_{RRM}	Peak repetitive reverse voltage						
V_{RWM}	Working peak reverse voltage	30	35	40	45	50	V
V_R	DC blocking voltage						
$V_{R(RMS)}$	RMS reverse voltage	21	24.5	28	31.5	35	V
I_o	Average rectified output current			30			A
I_{FSM}	Non-Repetitive peak forward surge current 8.3ms half sine wave			200			A
P_D	Power dissipation			2			W
$R_{\theta JA}$	Thermal resistance from junction to ambient			50			°C/W
T_j	Junction temperature			125			°C
T_{stg}	Storage temperature			-55~+150			°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Device	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(\text{BR})}$	MBR3030FCT	$I_R=1\text{mA}$	30			V
		MBR3035FCT		35			
		MBR3040FCT		40			
		MBR3045FCT		45			
		MBR3050FCT		50			
Reverse current	I_R	MBR3030FCT	$V_R=30\text{V}$			0.2	mA
		MBR3035FCT	$V_R=35\text{V}$				
		MBR3040FCT	$V_R=40\text{V}$				
		MBR3045FCT	$V_R=45\text{V}$				
		MBR3050FCT	$V_R=50\text{V}$				
Forward voltage	V_{F1}	MBR3030-45FCT	$I_F=15\text{A}$			0.7	V
		MBR3050FCT				0.8	
	V_{F2}^*	MBR3030-45FCT	$I_F=30\text{A}$			0.84	V
		MBR3050FCT				0.95	
Typical total capacitance	C_{tot}^*	MBR3030-45FCT	$V_R=4\text{V}, f=1\text{MHz}$		450		pF
		MBR3050FCT			400		

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$.